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(71) Applicant: **APPLIED MATERIALS, INC.** [US/US]; 3050 Bowers Avenue, Santa Clara, California 95054 (US).

(72) Inventors: **RATHI, Sudha**; c/o Applied Materials, Inc., Law Dept., M/S 1269, 3050 Bowers Avenue, Santa Clara, California 95054 (US). **JOSHI, Unnati**; c/o Applied Materials, Inc., Law Dept., M/S 1269, 3050 Bowers Avenue, Santa Clara, California 95054 (US). **ZHONG, Guangyan**; c/o Applied Materials, Inc., Law Dept., M/S 1269, 3050 Bowers Avenue, Santa Clara, California 95054 (US). **MANNA, Pramit**; c/o Applied Materials, Inc., Law Dept., M/S 1269, 3050 Bowers Avenue, Santa Clara, California 95054 (US). **JANAKIRAMAN, Karthik**; c/o Applied Materials, Inc., Law Dept., M/S 1269, 3050 Bowers Avenue, Santa Clara, California 95054 (US).

(74) Agent: **DOUGHERTY, Chad M.** et al.; PATTERSON + SHERIDAN LLP, 24 GREENWAY PLAZA, SUITE 1600, HOUSTON, Texas 77046 (US).

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(54) Title: DEPOSITION OF RESIST UNDERLAYER WITH REDUCED SP2 CARBON CONTENT

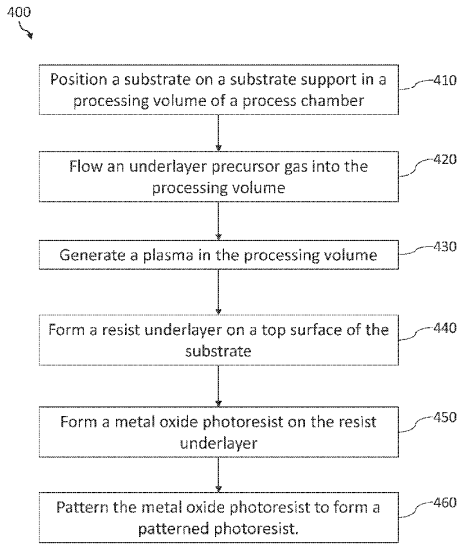


FIG. 4

(57) Abstract: The present disclosure generally relates to the fabrication of integrated circuits. More particularly, embodiments described herein provide techniques for forming resist underlayers having reduced sp2 hybridized carbon content for improving EUV lithography performance. In one embodiment, a method of processing a substrate is provided. The method includes flowing an underlayer precursor gas into a process chamber having a substrate and generating a plasma in the process chamber by applying a first RF bias for forming a resist underlayer on the substrate.

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